

FAST THYRISTORS

FOR MEDIUM FREQUENCY

KEY FEATURES

- ◆ Distributed amplifying gate design
- ◆ Low switching losses
- ◆ High di_T/dt -capability
- ◆ Precision control of Q_{RR} and V_{TM}
- ◆ Lifetime control irradiation technology
- ◆ Press-pack design



Type	V_{DRM}, V_{RRM}	$I_{T(AV)}$	I_{TSM}	$V_{T(TO)}$	r_T	$(di_T/dt)_{cr}$	$(dv_D/dt)_{cr}$	t_q	$R_{th(j-c)}$	T_{jmax}	F
		($T_c, ^\circ C$)	$t_p=10ms$	T_{jmax}	T_{jmax}	T_{jmax}	T_{jmax}	T_{jmax}			
		A	kA	V	m Ω	A/ μs	V/ μs	μs			
TFI353-1250	1500	1716(55) 1250(80)	21.0	1.15	0.210	1000	1000	20	0.0200	125	21
TFI353-1000	2200	1510(55) 1095(80)	17.0	1.36	0.257	1000	1000	50	0.0200	125	21
TFI173-2000	2200	3207(55) 2344(80)	43.0	1.42	0.145	1000	1000	50	0.0085	125	45
TFI283-2500	1400	3120(55) 2283(80)	50.0	1.54	0.164	1000	1000	10	0.0080	125	70
TFI183-2500	2400	3444(55) 2500(80)	55.0	1.47	0.126	1000	1000	50	0.0080	125	70
TFI193-2500	2800	3851(55) 2888(80)	72.5	1.20	0.168	1000	1000	70	0.0065	125	80

Development and delivery of thyristors in accordance with Customer technical requirements

TYPICAL APPLICATIONS

- ◆ Induction melting
- ◆ Industrial drives
- ◆ Resonant power supplies



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